

Photocouplers Infrared LED & Photo IC

TLP2348

1. Applications

- · Intelligent Power Module Signal Isolation
- · Programmable Logic Controllers (PLCs)
- · High-Speed Digital Interfacing for Instrumentation and Control Devices

2. General

The Toshiba TLP2348 consists of high-output an Infrared LED coupled with a high-gain, high-speed photo detector. It is housed in the SO6 package. This product can operate in power supply voltage 4.5 V to 30 V with the maximum operative temperature of 110 °C. Since TLP2348 has guaranteed 3 mA low supply current (I_{CCL}/I_{CCH}), and 1.6 mA low threshold input current (I_{FHL}), it contributes to energy saving of devices. It can drive directly from a microcomputer for a low input current. The detector has a totem-pole output stage with current sourcing and sinking capabilities. The TLP2348 has an internal Faraday shield that provides a guaranteed common-mode transient immunity of $\pm 30~\rm kV/\mu s$. The TLP2348 has an inverter output. A buffer output version, the TLP2345, is also available.

3. Features

- (1) Inverter logic type (Totem pole output)
- (2) Package: SO6
- (3) Operating temperature: -40 to 110 °C
- (4) Supply voltage: 4.5 to 30 V
- (5) Threshold input current: 1.6 mA (max)
- (6) Supply current: 3 mA (max)
- (7) Propagation delay time: 120 ns (max)
- (8) Pulse width distortion: 40 ns (max)
- (9) Common-mode transient immunity: ±30 kV/µs (min)
- (10) Isolation voltage: 3750 Vrms (min)
- (11) Safety standards

UL-recognized: UL 1577, File No.E67349

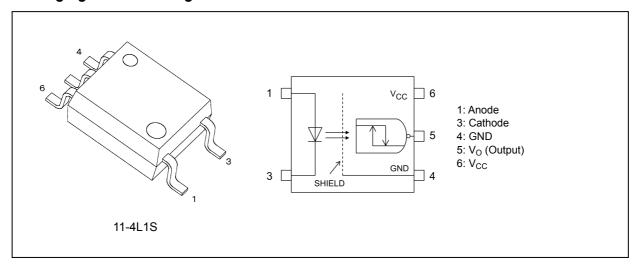
cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN IEC 60747-5-5, EN IEC 62368-1 (Note 1)

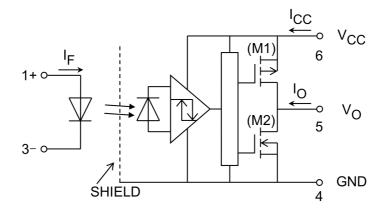
Note 1: When a VDE approved type is needed, please designate the Option (V4).



4. Packaging and Pin Assignment



5. Internal Circuit (Note)



Note: A 0.1- μF bypass capacitor must be connected between pin 6 and pin 4.

6. Principle of Operation

6.1. Truth Table

Input	LED	Output
Н	ON	L
L	OFF	Н

6.2. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	5.0	mm
Clearance distances	5.0	
Internal isolation thickness	0.4	



7. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I _F		15	mA
	Input forward current derating	(T _a ≥ 110 °C)	$\Delta I_F/\Delta T_a$		-0.33	mA/°C
	Peak transient input forward current		I _{FPT}	(Note 1)	1	Α
	Input reverse voltage		V_R		5	V
	Input power dissipation		P_D		40	mW
	Input power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_D/\Delta T_a$		-0.89	mW/°C
Detector	Output current		I _O		50 / -50	mA
	Output voltage		Vo		-0.5 to 30	V
	Supply voltage		V _{CC}		-0.5 to 30	V
	Output power dissipation		Po		100	mW
	Output power dissipation derating	(T _a ≥ 75 °C)	$\Delta P_{O}/\Delta T_{a}$		-2.0	mW/°C
Common	Operating temperature		T _{opr}		-40 to 110	°C
	Storage temperature		T _{stg}		-55 to 125	°C
	Lead soldering temperature	(10 s)	T _{sol}		260	°C
	Isolation voltage	(AC, 60 s, R.H. ≤ 60 %)	BV _S	(Note 2)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) \leq 1 μ s, 300 pps

Note 2: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Тур.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1)	2	_	10	mA
Input off-state voltage	$V_{F(OFF)}$		0		0.8	V
Supply voltage	V _{CC}	(Note 2)	4.5	_	30	
Operating temperature	T _{opr}	(Note 2)	-40	_	110	℃

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this data sheet should also be considered.

Note: A ceramic capacitor $(0.1 \, \mu F)$ should be connected between pin 6 and pin 4 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μs .

Note 2: Denotes the operating range, not the recommended operating condition.



9. Electrical Characteristics (Note) (Unless otherwise specified, T_a = -40 to 110 °C, V_{CC} = 4.5 to 30 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input forward voltage	V_{F}		_	I _F = 3 mA, T _a = 25 °C	1.35	1.55	1.65	V
Input forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$		_	I _F = 3 mA	_	-2.0	_	mV/°C
Input reverse current	I _R		_	V _R = 5 V, T _a = 25 °C	_		10	μА
Input capacitance	Ct		_	V = 0 V, f = 1 MHz, T _a = 25 °C	_	20	_	pF
Low-level output voltage	V _{OL}		Fig.	I _F = 3 mA, I _O = 3.5 mA	_	0.026	0.2	V
			12.1.1	I _F = 3 mA, I _O = 6.5 mA	_	0.047	0.4	
High-level output voltage	V _{OH}		Fig. 12.1.2	$V_F = 0.8 \text{ V}, I_O = -3.5 \text{ mA}$	V _{CC} - 0.2	V _{CC} - 0.03		
				$V_F = 0.8 \text{ V}, I_O = -6.5 \text{ mA}$	V _{CC} - 0.4	V _{CC} - 0.05	_	
Low-level supply current	I _{CCL}		Fig.	$I_F = 3 \text{ mA}, V_{CC} = 5.5 \text{ V}$	_	2.1	3	mA
			12.1.3	$I_F = 3 \text{ mA}, V_{CC} = 30 \text{ V}$	_	2.35	3	
High-level supply current	I _{CCH}		Fig.	V _{CC} = 5.5 V	_	2.1	3	
			12.1.4	V _{CC} = 30 V	_	2.35	3	
Low-level short-circuit output current	I _{OSL}	(Note 1)	Fig. 12.1.5	$I_F = 3 \text{ mA}, V_{CC} = V_O = 5.5 \text{ V}$	150	270	_	
				$I_F = 3 \text{ mA}, V_{CC} = V_O = 20 \text{ V}$	160	300	_	
High-level short-circuit	I _{OSH}	(Note 1)	Fig.	V _{CC} = 5.5 V, V _O = 0 V	_	-310	-150	
output current			12.1.6	V _{CC} = 20 V, V _O = 0 V	_	-330	-160	
Threshold input current (H/L)	I _{FHL}		_	I_{O} = 3.5 mA, V_{O} < 0.2 V, V_{CC} = 5 V	_	0.4	1.6	
Input current hysteresis	I _{HYS}		_	I _O = 3.5 mA	_	0.1	_	
Threshold input voltage (L/H)	V _{FLH}			I_{O} = -6.5 mA, V_{O} > (V_{CC} - 0.4)	0.8	1	_	V

Note: All typical values are at V_{CC} = 5 V, T_a = 25 °C, unless otherwise noted.

Note 1: I_O application time \leq 10 μs ; single pulse.

10. Isolation Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Total capacitance (input to output)	C _S	(Note 1)	V = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	(Note 1)	V = 500 V, R.H. ≤ 60 %	10 ¹²	1014	_	Ω
Isolation voltage	BVs	(Note 1)	AC, 60 s	3750	_	_	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.



11. Switching Characteristics (Note) (Unless otherwise specified, T_a = -40 to 110 °C, V_{CC} = 4.5 to 30 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig.	$I_F = 0 \rightarrow 3 \text{ mA}$	35	61	120	ns
Propagation delay time (L/H)	t _{pLH}		12.1.7, Fig.	$I_F = 3 \rightarrow 0 \text{ mA}$	35	65	120	
Pulse width distortion	t _{pHL} -t _{pLH}		12.1.8	I _F = 3 mA	_	4	40	
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)		I _F = 3 mA	-70		70	
Fall time	t _f	(Note 1)		$I_F = 0 \rightarrow 3 \text{ mA}$	_	3	30	
Rise time	t _r			$I_F = 3 \rightarrow 0 \text{ mA}$	_	3	30	
High-level common-mode transient immunity	CM _H		Fig. 12.1.9	I _F = 0 mA, V _{CC} = 30 V, V _{CM} = 1500 V _{p-p} , T _a = 25 °C	±30	±50	1	kV/μs
Low-level common-mode transient immunity	CM _L			I _F = 3 mA, V _{CC} = 30 V, V _{CM} = 1500 V _{p-p} , T _a = 25 °C	±30	±50		

Note: All typical values are at V_{CC} = 5 V, T_a = 25 °C, unless otherwise noted.

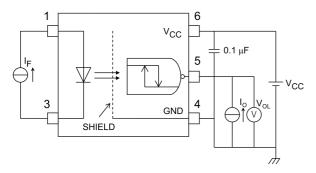
Note 1: f = 50 kHz, duty = 50 %, input current $t_r = t_f = 5$ ns or less, C_L is less than 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc.).



12. Test Circuits and Characteristics Curves

12.1. Test Circuits



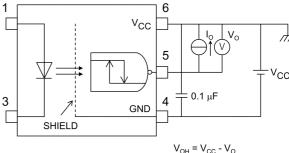
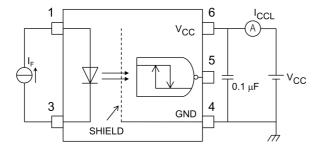


Fig. 12.1.1 V_{OL} Test Circuit

h V_{CC} $V_{OH} = V_{CC} - V_{O}$

Fig. 12.1.2 V_{OH} Test Circuit



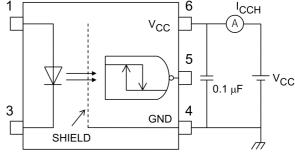
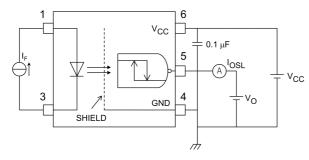


Fig. 12.1.3 I_{CCL} Test Circuit

Fig. 12.1.4 I_{CCH} Test Circuit



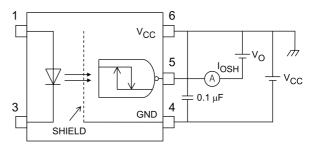


Fig. 12.1.5 IOSL Test Circuit

Fig. 12.1.6 IOSH Test Circuit

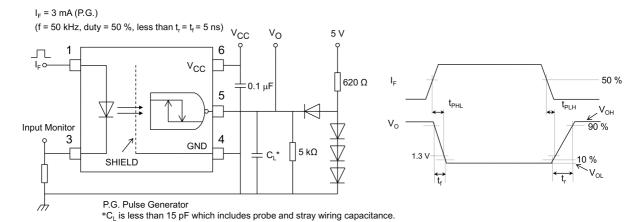


Fig. 12.1.7 Switching Time Test Circuit and Waveform



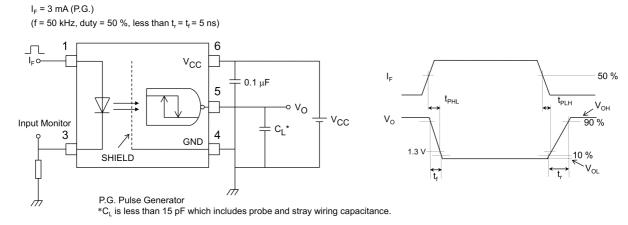


Fig. 12.1.8 Switching Time Test Circuit and Waveform

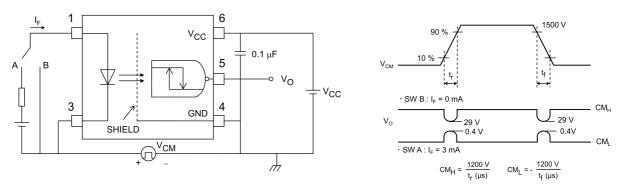
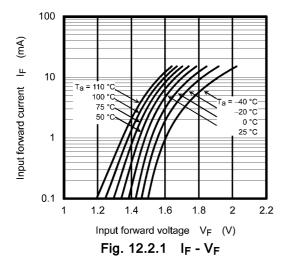


Fig. 12.1.9 Common-Mode Transient Immunity Test Circuit and Waveform



12.2. Characteristics Curves (Note)



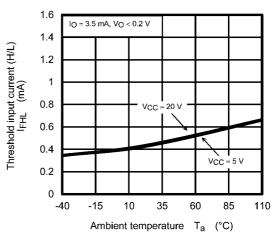
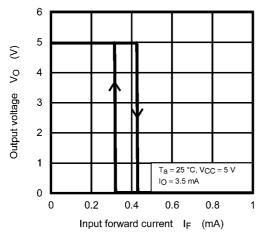


Fig. 12.2.2 I_{FHL} - T_a

24

20



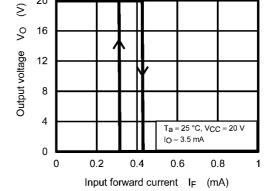
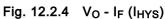
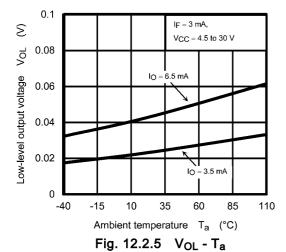


Fig. 12.2.3 V_O - I_F (I_{HYS})





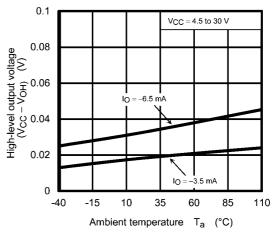
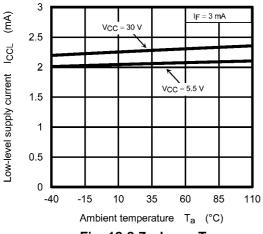
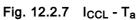


Fig. 12.2.6 (V_{CC}-V_{OH}) - T_a

Rev.6.0







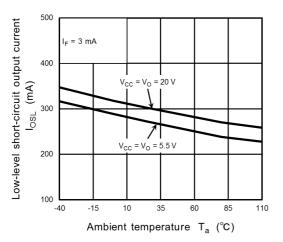


Fig. 12.2.9 I_{OSL} - T_a

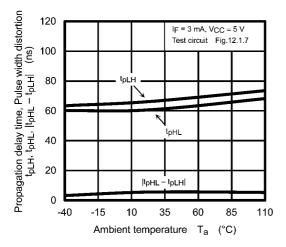


Fig. 12.2.11 t_{pLH} , t_{pHL} , $|t_{pHL}-t_{pLH}|$ - T_a (Test Circuit Fig. 12.1.7)

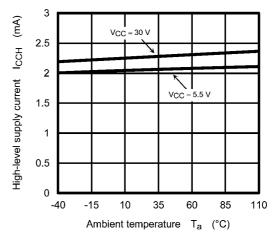


Fig. 12.2.8 I_{CCH} - T_a

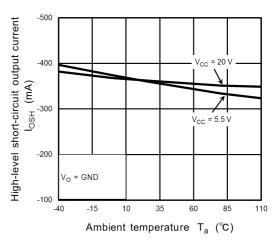


Fig. 12.2.10 I_{OSH} - T_a

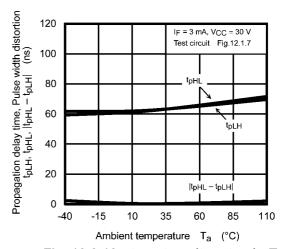
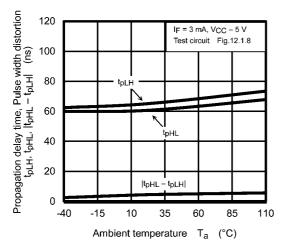
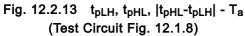


Fig. 12.2.12 t_{pLH} , t_{pHL} , $|t_{pHL}-t_{pLH}|$ - T_a (Test Circuit Fig. 12.1.7)







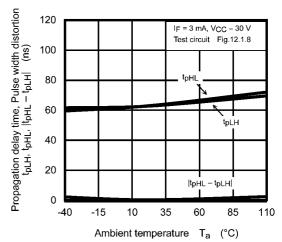


Fig. 12.2.14 t_{pLH} , t_{pHL} , $|t_{pHL}-t_{pLH}|$ - T_a (Test Circuit Fig. 12.1.8)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

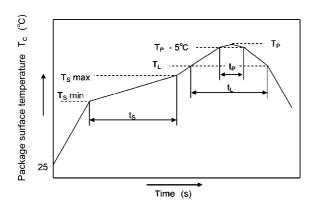
· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	s
Ramp-up rate (T _L to T _P)			3	°C/s
Liquidus temperature	TL	2	17	°C
Time above T _L	t _L	60	150	s
Peak temperature	T _P		260	°C
Time during which T_c is between $(T_P - 5)$ and T_P	t₽		30	s
Ramp-down rate (T _P to T _L)			6	°C/s

An Example of a Temperature Profile When Lead(Pb)-free Solder Is Used

· When using soldering flow

Preheat the device at a temperature of 150 $^{\circ}\text{C}$ (package surface temperature) for 60 to 120 seconds.

Mounting condition of 260 °C within 10 seconds is recommended.

Flow soldering must be performed once.

· When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

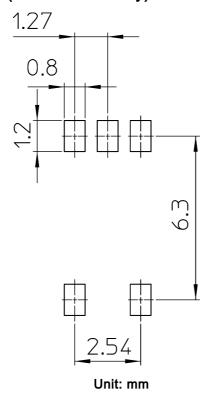
Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

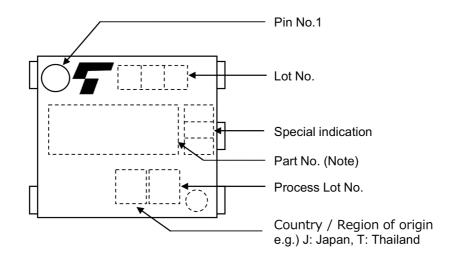
- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the devices in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the devices in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.



14. Land Pattern Dimensions (for reference only)



15. Marking





16. EN IEC 60747-5-5 Option (V4) Specification

· Part number: TLP2348 (Note 1)

• The following part naming conventions are used for the devices that have been qualified according to option (V4) of EN IEC 60747.

Example: TLP2348(V4-TPL,E

V4: EN IEC 60747 option

TPL: Tape type

E: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP2348(V4-TPL,E → TLP2348

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification			
for rated mains voltage ≤ 150 Vrms for rated mains voltage ≤ 300 Vrms		I-IV I-III	_
Climatic classification		40 / 110 / 21	_
Pollution degree		2	_
Maximum operating insulation voltage	VIORM	707	Vpeak
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM} , type and sample test t_p = 10 s, partial discharge < 5 pC	V _{pr}	1131	Vpeak
Input to output test voltage, Method B V_{pr} = 1.875 × V_{IORM} , 100 % production test t_p = 1 s, partial discharge < 5 pC	V _{pr}	1325	Vpeak
Highest permissible overvoltage (transient overvoltage, t _{pr} = 60 s)	VTR	6000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I _F , P _{SO} = 0) power (output or total power dissipation) temperature	I _{si} P _{so} T _s	250 400 150	mA mW °C
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R _{si}	$\geq 10^{12}$ $\geq 10^{11}$ $\geq 10^{9}$	Ω

Fig. 16.1 EN IEC 60747 Isolation Characteristics



Minimum creepage distance	Cr	5.0 mm
Minimum clearance	СІ	5.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Fig. 16.2 Insulation Related Specifications (Note)

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 16.3 Marking on Packing

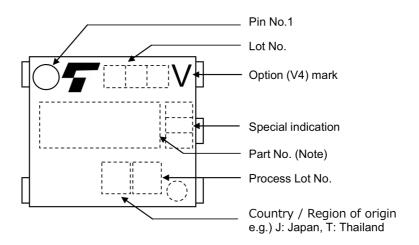
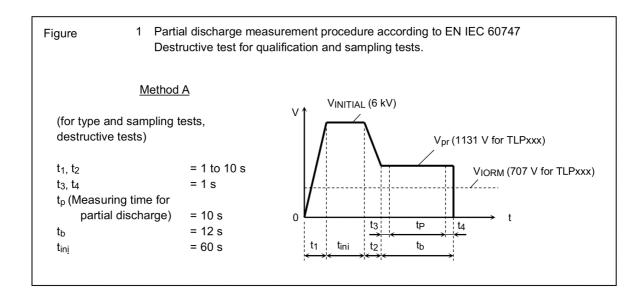
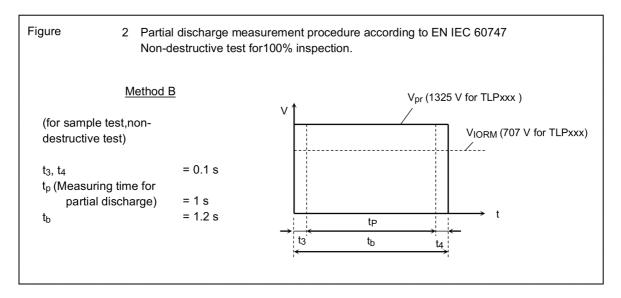


Fig. 16.4 Marking Example(Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (V4) of EN IEC 60747.







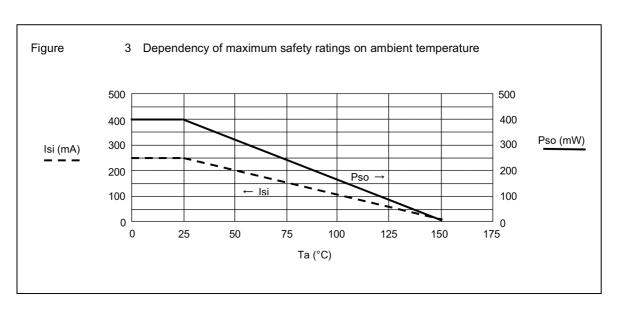


Fig. 16.5 Measurement Procedure



17. Ordering Information

When placing an order, please specify the part number, tape type and quantity as shown in the following example.

Example) TLP2348(TPL,E 3000 pcs

Part number: TLP2348

Tape type: TPL

[[G]]/RoHS COMPATIBLE: E (Note 1)

Quantity (must be a multiple of 3000): 3000 pcs

Note 1: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

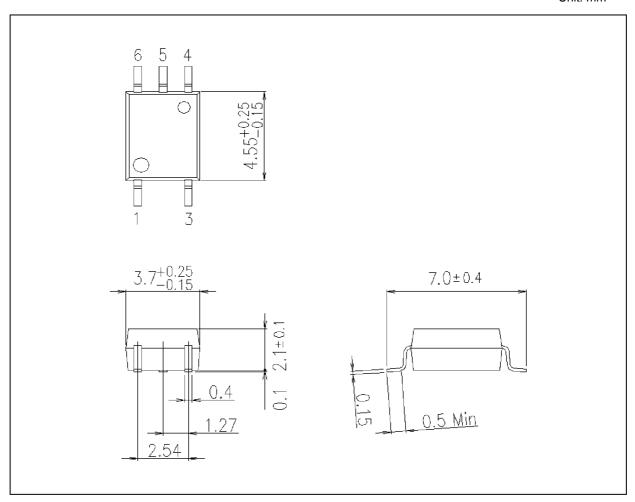
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Rev.6.0



Package Dimensions

Unit: mm



Weight: 0.08 g (typ.)

	Package Name(s)
TOSHIBA: 11-4L1S	

Rev.6.0



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